

## UNITED STATES DEPARTMENT OF COMMERCE **Patent and Trademark Office**

Address: COMMISSIONER OF PATENTS AND TRADEMARKS

Washington, D.C. 20231

FIRST NAMED INVENTOR ATTORNEY DOCKET NO. FILING DATE APPLICATION NO.

9976591.747 08/01/96 UHITANI 11

079777052001

SCOTT C HARRIS FISH & RICHARDSON 601 13TH STREET NW WASHINGTON DC 20005 IMI2/0215

**EXAMINER** 

KLINEMUND, R

ART UNIT

PAPER NUMBER

**DATE MAILED:** 

U2/15/00

H

Please find below and/or attached an Office communication concerning this application or proceeding.

**Commissioner of Patents and Trademarks** 

## Office Action Summary

Application No. 08/690,747

Applicant(s)

Ohtani et al

Examiner

Robert Kunemund

Group Art Unit 1765



X Responsive to communication(s) filed on Nov 24, 1999	
This action is <b>FINAL</b> .	
Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11; 453 O.G. 213.	
A shortened statutory period for response to this action is set to is longer, from the mailing date of this communication. Failure to application to become abandoned. (35 U.S.C. § 133). Extension 37 CFR 1.136(a).	respond within the period for response will educe the
Disposition of Claims	is the panding in the application
X Claim(s) <u>1-3, 5-8, 10-14, and 16-28</u>	is/are pending in the application.
Of the above, claim(s)	is/are withdrawn from consideration.
[] Claim(s)	is/are allowed.
X Claim(s) 1-3, 5-8, 10-14, and 16-28	is/are rejected.
Claim(s)	
Claims	
Application Papers	
See the attached Notice of Draftsperson's Patent Drawing	Review, PTO-948.
The drawing(s) filed on is/are objected	ed to by the Examiner.
The proposed drawing correction, filed on	is approved disapproved.
The specification is objected to by the Examiner.	
$oxedsymbol{\square}$ The oath or declaration is objected to by the Examiner.	
Priority under 35 U.S.C. § 119	
Acknowledgement is made of a claim for foreign priority to	
☐ All ☐ Some* ☐ None of the CERTIFIED copies of	the priority documents have been
received.	
$\square$ received in Application No. (Series Code/Serial Num	
$\square$ received in this national stage application from the	International Bureau (PCT Rule 17.2(a)).
*Certified copies not received:	
Acknowledgement is made of a claim for domestic priorit	y under 35 U.S.C. § 119(e).
Attachment(s)	
Notice of References Cited, PTO-892	
Information Disclosure Statement(s), PTO-1449, Paper N	O(S)
Interview Summary, PTO-413	18
Notice of Draftsperson's Patent Drawing Review, PTO-94	<del>,</del>
Notice of Informal Patent Application, PTO-152	
SEE OFFICE ACTION ON T	THE FOLLOWING PAGES

Application/Control Number: 08/690,747

Art Unit: 1763

The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

Claims 1, 6, 22, 23 and 26-28 are rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. There is no support in the specification as originally filed for the invention as is now claimed. There is no teaching that the silicon is to be considered at least a channel.

1. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321© may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 1-3, 5-8, 10-14, and 16 to 28 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-18 of U.S. Patent No. 5,580,792. Although the conflicting claims are not identical, they are not patentably distinct from

Application/Control Number: 08/690,747

Art Unit: 1763

each other because the sole difference is the place of etching. However, in the absence of unobvious results, it would have been obvious to one of ordinary skill in the art to determine through routine experimentation the optimum, operable placement of etching in order to remove metal or grain boundaries

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103© and potential 35 U.S.C. 102(f) or (g) prior art under 35 U.S.C. 103(a).

Claims 1-3, 5-8, 10-14, and 16 to 28 are rejected under 35 U.S.C. 103(a) as being unpatentable over Nakajima et al in view of Gibson.

The Nakajima et al reference teaches a method of silicon crystal growth. On a substrate, a catalyst for growth is applied. Then an amorphous layer is deposited onto the metal, the resulting structure is then annealed in order to crystallize the silicon. The silicon can be patterned to from

Page 3

Application/Control Number: 08/690,747

Art Unit: 1763

island. The sole difference between the instant claims and the prior art is the etching. However, the Gibson reference teaches a method of etching silicon layers which have been grown with a catalyst in the area of the catalyst, note col. 3. It would have been obvious to one of ordinary skill in the art to modify the Nakajima et al process by the teachings of the Gibson reference to etch in order to remove the metal catalyst which lower the output of the device formed on such layers.

Claims 1-3, 5-8, 10-14, and 16 to 28 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Patents 5,580,792

The 5,580,792 reference teaches a method of silicon crystal growth. On a substrate, a catalyst for growth is applied. Then an amorphous layer is deposited onto the metal, the resulting structure is then annealed in order to crystallize the silicon. The silicon can be patterned to from island and is etched after the heating step. The sole difference between the instant claims and the prior art is the etching placement. However, in the absence of unobvious results, it would have been obvious to one of ordinary skill in the art to determine through routine experimentation the optimum, operable placement of the etching in the 5,580,792 reference in order to form the desired island sizes and remove metals.

## Response to Applicant's Arguments

Applicant's arguments filed November 24, 1999 have been fully considered but they are not persuasive.

The rejection over the Nakajima et al reference will be maintained as the certified English translation of the foreign priority document submitted to the Patent Office does not teach the invention as is now claimed. The translation does not mention the silicon being at least a channel.

Applicants' argument concerning the 5,580,792 patent is noted. However, at col. 3 line 10-15 the reference does teach that the amorphous silicon layer is patterned prior to crystallization of said layer. Therefore, the rejection over this patent is maintained by the examiner of record. The rejections over the other two patents has been withdrawn in view of applicants arguments.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Robert Kunemund whose telephone number is (703) 308-1091. The examiner can normally be reached on Monday through Friday from 7:00 to 3:30.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Ben Utech can be reached on (703) 308-3324. The fax phone number for this Group is (703) 305-3599.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0661.

RMK

February 11, 2000